

## Direct observation of exchange-driven spin interactions in one-dimensional system

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We present experimental results of transverse electron focusing measurements performed on an n-type GaAs based mesoscopic device consisting of one-dimensional (1D) quantum wires as injector and detector. We show that non-adiabatic injection of 1D electrons at a conductance of  $\frac{e^2}{h}$  results in a single first focusing peak, which transforms into two asymmetric sub-peaks with a gradual increase in the injector conductance up to  $\frac{2e^2}{h}$ , each sub-peak representing the population of spin-state arising from the spatially separated spins in the injector. Further increasing the conductance flips the spin-states in the 1D channel, thus reversing the asymmetry in the sub-peaks. On applying a source-drain bias, the spin-gap, so obtained, can be resolved, thus providing evidence of exchange interaction induced spin polarization in the 1D systems. © 2017 Author(s). All article content, except where otherwise noted, is licensed under a Creative Commons Attribution (CC BY) license (<http://creativecommons.org/licenses/by/4.0/>). [<http://dx.doi.org/10.1063/1.4989374>]

Spintronics involves engineering the spin degrees of freedom to replace charges with spins to carry information precisely to meet the future technological challenges. This has led to a volume of theoretical<sup>1</sup> and experimental work on spin based systems, exploiting the spin-orbit interaction and the spin-Hall effect using low dimensional semiconductors and optical systems.<sup>2–7</sup> Among various quantum systems, a simple yet powerful system is a one-dimensional (1D) quantum wire realised using a pair of split gates,<sup>8</sup> resulting in the evolution of spin degenerate 1D subbands as the confinement potential is relaxed.<sup>9–11</sup> One of the merits of this system is that the spin degeneracy can be easily lifted on application of an in-plane magnetic field<sup>12</sup> such that spin-up and spin-down electrons could be energetically separated. However, it is also predicted that the exchange can induce partial spin polarization; in other words, it creates a spin-gap in the ground state of a longer 1D system.<sup>13,14</sup> The origin of spin-gap in the 1D system has aroused a great interest to explain the “0.7 anomaly” in the framework of spin correlation between the 1D electrons.<sup>13–16</sup>

The spin polarization in a 1D quantum wire<sup>13,14</sup> can be measured by means of transverse electron focusing (TEF),<sup>17–19</sup> where the height of each focusing peak is proportional to the population of detected electrons. It has been confirmed experimentally in a GaAs hole gas<sup>20,21</sup> and an InSb electron gas<sup>22</sup> that the first focusing peak splits into two sub-peaks and each peak is associated with a spin of an electron. In this work, we provide direct evidence by means of focusing measurements

using electrons in the GaAs/AlGaAs heterostructure that the spin-gap can be detected precisely up to the first excited state in agreement with observations of the “0.7” and “1.7” structures.<sup>12,24</sup> Furthermore, we show an effect in which spin repulsion due to the exchange interaction results in flip-flop of the spin-states. In addition, we have combined the source-drain bias spectroscopy with the focusing measurement and provide further evidence of the spin-gap in the 1D system.

The devices studied in the present work were fabricated from the high mobility two dimensional electron gas (2DEG) formed at the interface of the GaAs/Al<sub>0.33</sub>Ga<sub>0.67</sub>As heterostructure. At 1.5 K, the measured electron density (mobility) was  $1.80 \times 10^{11} \text{ cm}^{-2}$  ( $2.17 \times 10^6 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ); therefore, the mean free path is over  $10 \mu\text{m}$  which is much larger than the electron propagation length. The experiments were performed using a cryofree dilution refrigerator with a lattice temperature of 20 mK by the standard lockin technique.

The focusing device is specially designed so that the injector and the detector can be separately controlled to avoid a possible cross-talking between them using a 90° geometry.<sup>17,25</sup> The linear focusing devices<sup>17,20–22,25</sup> used in previous work share the center gate which may introduce a lateral electric field along the confinement direction. Figure 1 shows the experimental setup along with a typical focusing spectrum obtained using the device shown in the inset. The quantum wire used for the injector and detector has a width (confinement direction) of 500 nm and a length (current flow direction) of 800 nm. It may be noted that the quasi-1D quantum wire (in the regime defined between the injector and detector quantum wires, highlighted by the red arrow in Fig. 1) has a smaller lithographic size than the injector/detector quantum wires, and thus, within the studied injector/detector gate voltage, this quasi-1D quantum wire is in the pinch-off regime and so fully reflects the focused electrons.

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